PCN Number:			20220718001.2					PCN Da	PCN Date: July 1			9, 2022				
Title	e:	Qı	ualifica	ation	ion of STATS ChipPac as an additional assembly site for selected Devices						selected Devices					
Customer Contact: PCN Manage							De	Dept: Quality Services								
Proposed 1 st Ship Date: Jan 14							4, 202	, 2023 Sample Req accepted					Aug 19, 2022*			
*Sa	*Sample requests received after Aug 19, 2022 will not be supported.															
Cha	nge	Ту	pe:													
Assembly Site						☐ Design ☐						Wafer Bump Site				
Assembly Process						Data Sheet					Wafer Bump Material					
Assembly Materials						Part number change					Ц	Wafer Bump Process				
Ш			ical S					est Si				Щ		r Fab Site		
Ш	Pack	king	J/Ship	ping/	Labeli	ing	Te	est Pr	OCE	ess		<u>Ц</u>		Wafer Fab Materials		
								Wafer Fab Process								
	PCN Details															
Des	Description of Change:															
Texas Instruments Incorporated is announcing the qualification of STATS ChipPac as an alternate Assembly site for devices listed below in the product affected section. There are no construction differences of the devices between the two assembly sites.																
Rea	Reason for Change:															
Supply continuity																
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																
None																
Impact on Environmental Ratings																
Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.																
						R	EACH	EACH Green Status						IEC 62474		
No Change ■ No Change No Change ■ No Change N					⊠ No Cha					No Chan	ige			No Change		
Cha	nge	s to	prod	luct i	ident	ificatio	on res			rom this PC			T			
As	sseml	bly S	Site	Asse	Assembly Site Ori			L) A	sser	mbly Country	bly Country Code (23L)			Assembly City		
Amkor					AMP			KOR						Gwangju		
STATS ChipPac SCK								KOR						INCHEON		
IN MAD 2DO MSL MSL OPT ITE	TEX STRUIDE IN:	(AS MEN : Ma 2600 2350		39 SEAL	G4 DT 19/04	el (no	ot actu	400	(1P (Q (31 (4W (P) (2P) (20)	T)LOT: 395 ') TKY(1T) 7 REV: (V) CSO: SHE (2	(D) 9047 7523	7ML 483	A 3SI2 317 USA			

Product Affected:									
DRA829JMT0BALFQ1	DRA829VMTGBALF	TDA4VM88TCBALFQ1	TDA4VM88TGBALFR						
DRA829JMT0BALFRQ1	DRA829VMTGBALFQ1	TDA4VM88TCBALFRQ1	TDA4VM88TGBALFRQ1						
DRA829JMTGBALF	DRA829VMTGBALFRQ1	TDA4VM88TGBALF	TDA4VM88TRBALFQ1						
DRA829JMTGBALFQ1	TDA4VM88T5BALFQ1	TDA4VM88TGBALFQ1	TDA4VM88TRBALFRQ1						
DRA829JMTGBALFRQ1	TDA4VM88T5BALFRQ1								



TI Information Selective Disclosure

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Jacinto7- DRA829xxx and TDA4VM88xxx

Product Attributes

Attributes	Test Vehicle: DC2AAALF	Qual Device: XJ721EGALF (ES 1.0)	Qual Device: XJ721EGALF (ES 1.1)	Qual Device: XJ721EGALF (ES 1.2)	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	
Product Function	Microprocessor	Microprocessor	Microprocessor	Microprocessor	
Wafer Fab Supplier	TSMC-F14	TSMC-F14	TSMC-F14	TSMC-F14	
Assembly Site	SCK	SCK	SCK	SCK	
Package Type	Flip Chip BGA	Flip Chip BGA	Flip Chip BGA	Flip Chip BGA	
Package Designator	ALF	ALF	ALF	ALF	
Ball/Lead Count	827	827	827	827	

⁻ QBS: Qual By Similarity

⁻ Qual Device XJ721EGALF is qualified at LEVEL3-250C

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Test Vehicle: DC2AAALF	Qual Device: XJ721EGALF (ES 1.0)	Qual Device: XJ721EGALF (ES 1.1)	Qual Device: XJ721EGALF (ES 1.2)
					Test Group A – A	Accelerated Environ	ment Stress Test	s		
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	(level 3 @ 250C peak +5/-0C)	-	3/982/0		
THB	A2	JEDEC JESD22- A101	3	77	**Auto Biased Temp Humidity	85C/85%RH, (1000 Hours)	-	3/231/0		
UHST	А3	JEDEC JESD22- A102, A118, or A101	3	77	**Unbiased HAST	110C/85%RH (264 Hours)		3/231/0		
TC	A4	JEDEC JESD22- A104 and Appendix 3	3	77	**T/C -55C/125C	-55C/+125C (1000 Cycles)	-	3/231/0 (c)		
PTC	A5	JEDEC JESD22- A105	1	45	**Power Temperature Cycle	-40C/105C (1000 Cycles)	-	1/45/0		
HTSL	A6	JEDEC JESD22- A103	1	45	**High Temp. Storage Bake	150C (1000 Hours)	-	1/77/0 (c)		
		IEDEA			Test Group B – A	Accelerated Lifetime	Simulation Test	S		
HTOL	B1	JEDEC JESD22- A108	3	77	HTOL - CMOS	132C Tj (1000 Hours)	-		3/231/1 (a)	
ELFR	B2	AEC Q100- 008	3	800	EFR2	135C Tj (48 Hours)	-		2/1630/0	1/811/2 (b)
		IEDEO			Test Group C	– Package Assemb	y Integrity Tests			
PD	C4	JEDEC JESD22- B100 and B108	3	10	Test Group C Physical Dimensions (Cpk>1.67)	– Package Assemb -	y Integrity Tests -	3/30/0	_	-
PD SBS	C4	JESD22- B100 and	3	10 50	Physical Dimensions	- Package Assemb Solder Balls	y Integrity Tests -		-	-
		JESD22- B100 and B108 AEC Q100-			Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67)	-	-	3/30/0 3/150/0	-	-
		JESD22- B100 and B108 AEC Q100-			Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration	- Solder Balls	Reliability Tests	3/30/0 3/150/0 (BGAs)	- s Technology Rec	- quirements
SBS	C5	JESD22- B100 and B108 AEC Q100- 010 JESD61		50	Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I	- Solder Balls	- Reliability Tests Com	3/30/0 3/150/0 (BGAs) pleted Per Proces	s Technology Rec	-
SBS	C5	JESD22- B100 and B108 AEC Q100- 010 JESD61	3	50	Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection Carrier	- Solder Balls	- Celiability Tests Com	3/30/0 3/150/0 (BGAs) pleted Per Proces		quirements
SBS EM TDDB	C5	JESD22- B100 and B108 AEC Q100- 010 JESD61 JESD65	-	50 - -	Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection	Solder Balls — Die Fabrication I —	Reliability Tests Comp	3/30/0 3/150/0 (BGAs) pleted Per Proces	s Technology Rec	quirements
SBS EM TDDB HCI	C5 D1 D2 D3	JESD22- B100 and B108 AEC Q100- 010 JESD61 JESD65			Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration	Solder Balls D – Die Fabrication f - - - - -	Comp	3/30/0 3/150/0 (BGAs) Dieted Per Proces Dieted Per Proces Dieted Per Proces	s Technology Rec	quirements quirements
SBS EM TDDB HCI NBTI	C5 D1 D2 D3 D4	JESD22- B100 and B108 AEC Q100- 010 JESD61 JESD65 JESD60 & 28			Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration	Solder Balls D – Die Fabrication F - - - - - - - - - - - - -	Comp	3/30/0 3/150/0 (BGAs) Dieted Per Proces Dieted Per Proces Dieted Per Proces	s Technology Rec	quirements quirements
SBS EM TDDB HCI NBTI	C5 D1 D2 D3 D4	JESD22- B100 and B108 AEC Q100- 010 JESD61 JESD65 JESD60 & 28 - - - AEC Q100- 011			Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration	Solder Balls D – Die Fabrication f - - - - -	Comp	3/30/0 3/150/0 (BGAs) Dieted Per Proces Dieted Per Proces Dieted Per Proces	s Technology Rec	quirements quirements
SBS EM TDDB HCI NBTI SM	C5 D1 D2 D3 D4 D5	JESD22- B100 and B108 AEC Q100- 010 JESD61 JESD65 JESD60 & 28	3 - - -		Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration Test Group	Solder Balls D – Die Fabrication f - - - - E – Electrical Verit 500V, 750V (corner pins)	Comp	3/30/0 3/150/0 (BGAs) pleted Per Proces pleted Per Proces pleted Per Proces pleted Per Proces	s Technology Rec s Technology Rec s Technology Rec	quirements quirements quirements
SBS EM TDDB HCI NBTI SM CDM	C5 D1 D2 D3 D4 D5 E3	JESD22- B100 and B108 AEC Q100- 010 JESD61 JESD65 & 28 - - - AEC Q100- 011 AEC Q100- 011	1	50 - - - - - 3	Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration Test Group Auto ESD CDM Electrical Char.	Solder Balls D – Die Fabrication f - - - - - D E – Electrical Verif 500V, 750V (corner pins) - Additional Tests	Comparition Tests	3/30/0 3/150/0 (BGAs) pleted Per Proces	s Technology Rec	quirements quirements quirements quirements
SBS EM TDDB HCI NBTI SM CDM	C5 D1 D2 D3 D4 D5 E3	JESD22- B100 and B108 AEC Q100- 010 JESD61 JESD65 & 28 - - - AEC Q100- 011 AEC Q100- 011	1	50 - - - - - 3	Physical Dimensions (Cpk>1.67) Solder Ball Shear (Cpk>1.67) Test Group I Electromigration Time Dependant Dielectric Breakdown Hot Injection Carrier Negative Bias Temperature Instability Stress Migration Test Group Auto ESD CDM	Solder Balls D – Die Fabrication f - - - - E – Electrical Verit 500V, 750V (corner pins)	Comparition Tests	3/30/0 3/150/0 (BGAs) pleted Per Proces	s Technology Rec	quirements quirements quirements quirements

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/UHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20180413-125477

Note:

- (a) 8D reports available on request.
- (b) 8D reports available on request.
- (c) Electrically Induced Physical Damage (EIPD)

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail				
WW Change Management Team	PCN www admin_team@list.ti.com				

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